Low-Voltage, 1-Ω, Dual SPDT Analog Switch

FEATURES

- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance - $r_{ON: 1.0}$ Ω
- –71 dB OIRR @ 2.7 V, 100 kHz
- MSOP-10 Package
- Available in Lead (Pb)-Free

BENEFITS

- Reduced Power Consumption
- High Accuracy
- Reduce Board Space
- 1.6-V Logic Compatible
- High Bandwidth

APPLICATIONS

- Cellular Phones
- Speaker Headset Switching
- Audio and Video Signal Routing
- PCMCIA Cards
- Battery Operated Systems
- Relay Replacement

DESCRIPTION

The DG2035 is a 1-Ω dual SPDT analog switch designed for low voltage applications.

The DG2035 has on-resistance matching (less than 0.05 Ω @ 2.7 V) and flatness (less than 0.2 Ω @ 2.7 V) that are guaranteed over the entire voltage range. Additionally, low logic thresholds makes the DG2035 an ideal interface to low voltage DSP control signals.

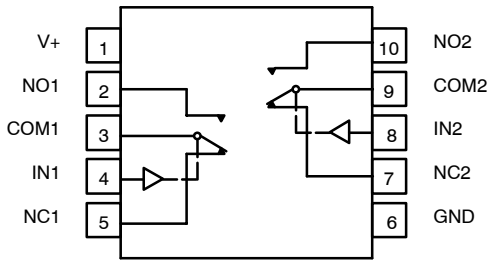
The DG2035 has fast switching speed (on/off time @ 34 and 24 ns) with break-before-make guaranteed. In the On condition, all switching elements conduct equally in both directions. Off-isolation and crosstalk is –71 dB @ 100 kHz.

The DG2035 is built on Vishay Siliconix's high-density low voltage CMOS process. An eptiaxial layer is built in to prevent latchup.

Packaged in space saving MSOP-10, the DG2035 is a high performance, low r_{ON} switch for battery powered applications. The DG2035 is available in both standard and lead (Pb)-free packaging. No lead is used in the manufacturing process, for the lead (Pb)-free version, either inside the device/package or on external terminations.

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

MSOP-10



Top View

TRUTH TABLE		
Logic	**NC1 and NC2**	**NO1 and NO2**
0	ON	OFF
1	OFF	ON

ORDERING INFORMATION			
Temp Range	**Package**	**Standard Part Number**	**Lead (Pb)-Free Part Number**
-40 to 85°C	MSOP-10 (with Tape and Reel)	DG2035DQ-T1	DG2035DQ-T1—E3

ABSOLUTE MAXIMUM RATINGS

Reference to GND

V+ . . . . . -0.3 to +6 V

IN, COM, NC, NO[a] . . . . . -0.3 to (V+ + 0.3 V)

Continuous Current (NO, NC, COM) . . . . . ±300 mA

Peak Current . . . . . ±500 mA

(Pulsed at 1 ms, 10% duty cycle)

Storage Temperature (D Suffix) . . . . . -65 to 150°C

ESD per Method 3015.7 . . . . . >2 kV

Power Dissipation (Packages)[b]

MSOP-10[c] . . . . . 320 mW

Notes:
a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
b. All leads welded or soldered to PC Board.
c. Derate 4.0 mW/°C above 70°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

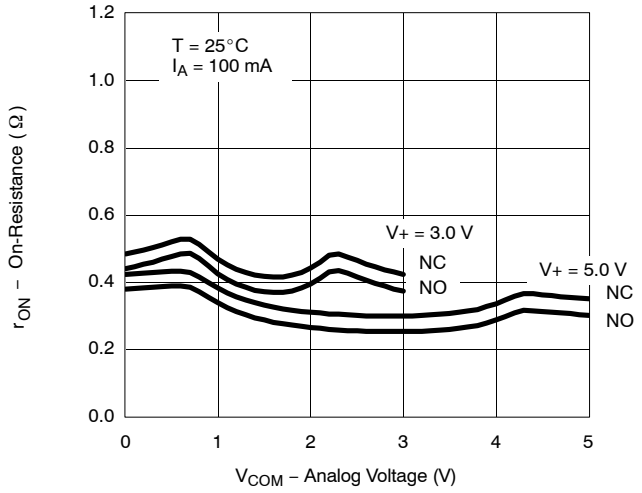
SPECIFICATIONS (V+ = 3 V)

Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3 V, ±10%, V_{IN} = 0.4 or 2.0 V[e]	Temp[a]	Limits −40 to 85°C Min[b]	Typ[c]	Max[b]	Unit
Analog Switch							
Analog Signal Range[d]	V_{NO}, V_{NC}, V_{COM}		Full	0		V+	V
On-Resistance	r_{ON}	V+ = 2.7 V, V_{COM} = 0.6/1.5 V, I_{NO}, I_{NC} = 100 mA	Room Full		0.7	1.0 1.2	Ω
r_{ON} Flatness[d]	r_{ON} Flatness		Room		0.12	0.2	
On-Resistance Match Between Channels[d]	$\Delta r_{DS(on)}$		Room			0.05	
Switch Off Leakage Current	$I_{NO(off)}$, $I_{NC(off)}$	V+ = 3.3 V, V_{NO}, V_{NC} = 0.3 V/3 V, V_{COM} = 3 V/0.3 V	Room Full	−2 −10		2 10	nA
	$I_{COM(off)}$		Room Full	−2 −10		2 10	
Channel-On Leakage Current	$I_{COM(on)}$	V+ = 3.3 V, V_{NO}, V_{NC} = V_{COM} = 0.3 V/3 V	Room Full	−2 −10		2 10	
Digital Control							
Input High Voltage[d]	V_{INH}		Full	1.6			V
Input Low Voltage	V_{INL}		Full			0.4	
Input Capacitance	C_{in}		Full		9		pF
Input Current	I_{INL} or I_{INH}	V_{IN} = 0 or V+	Full	1		1	µA
Dynamic Characteristics							
Turn-On Time	t_{ON}	V_{NO} or V_{NC} = 2.0 V, R_L = 50 Ω, C_L = 35 pF	Room Full		34	58 59	ns
Turn-Off Time	t_{OFF}		Room Full		24	49 50	
Break-Before-Make Time	t_d	V_{NO} or V_{NC} = 2.0 V, R_L = 50 Ω, C_L = 35 pF	Full	2	10		
Charge Injection[d]	Q_{INJ}	C_L = 1 nF, V_{GEN} = 1.5 V, R_{GEN} = 0 Ω	Room		4		pC
Off-Isolation[d]	OIRR	R_L = 50 Ω, C_L = 5 pF, f = 100 KHz	Room		−71		dB
Crosstalk[d]	X_{TALK}		Room		−71		
N_O, N_C Off Capacitance[d]	$C_{NO(off)}$	V_{IN} = 0 or V+, f = 1 MHz	Room		117		pF
	$C_{NC(off)}$		Room		115		
Channel-On Capacitance[d]	$C_{NO(on)}$		Room		367		
	$C_{NC(on)}$		Room		368		
Power Supply							
Power Supply Range	V+			1.8		5.5	V
Power Supply Current	I+	V_{IN} = 0 or V+	Full		0.01	1.0	µA

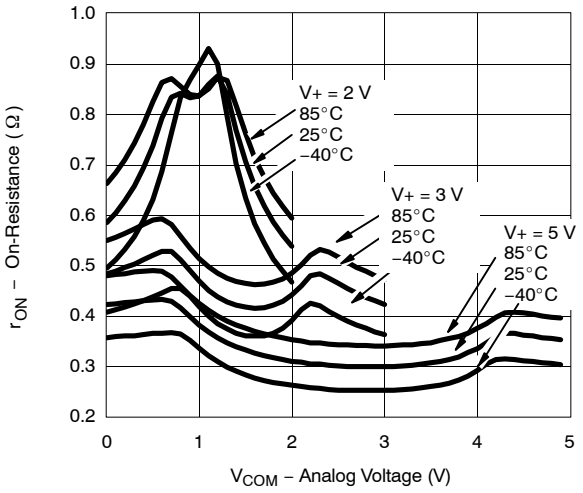
Notes:
a. Room = 25°C, Full = as determined by the operating suffix.
b. Typical values are for design aid only, not guaranteed nor subject to production testing.
c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
d. Guarantee by design, nor subjected to production test.
e. V_{IN} = input voltage to perform proper function.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

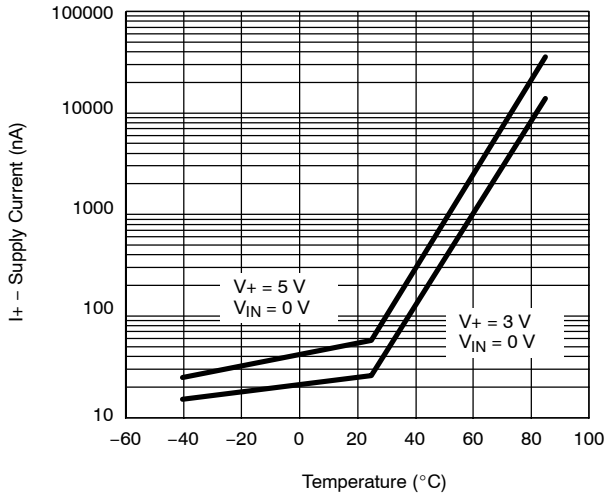
r_{ON} vs. V_{COM} and Supply Voltage



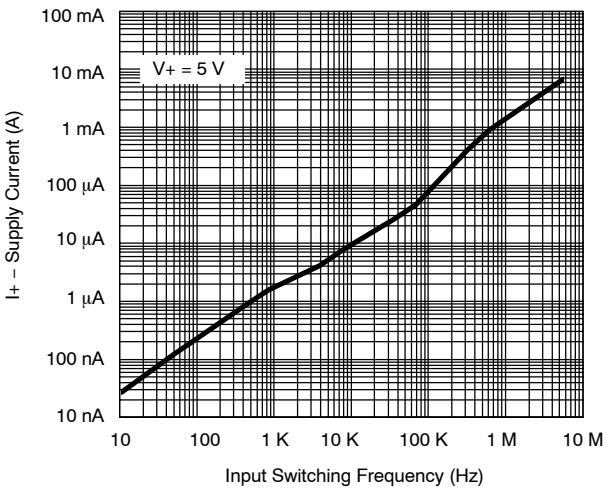
r_{ON} vs. Analog Voltage and Temperature (NC1)



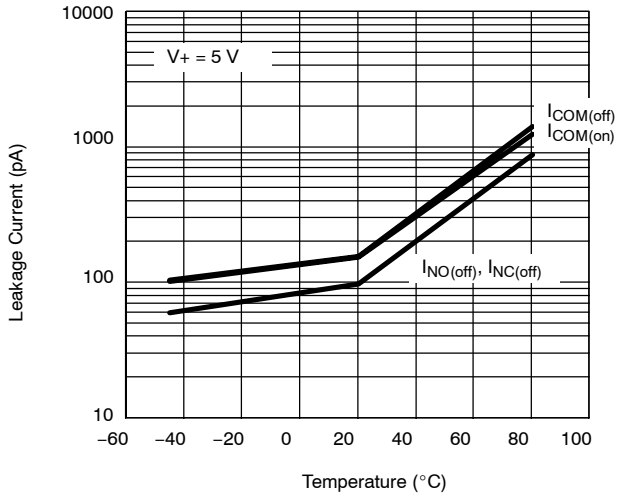
Supply Current vs. Temperature



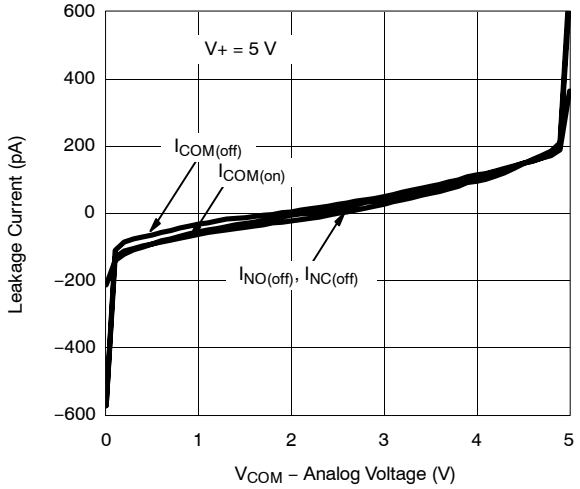
Supply Current vs. Input Switching Frequency



Leakage Current vs. Temperature

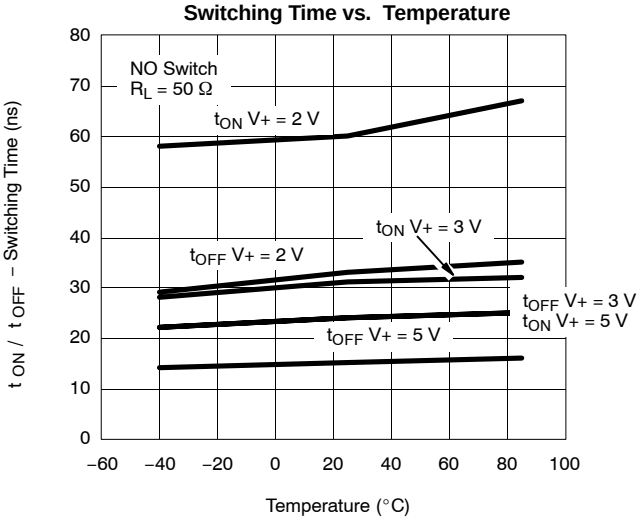


Leakage vs. Analog Voltage

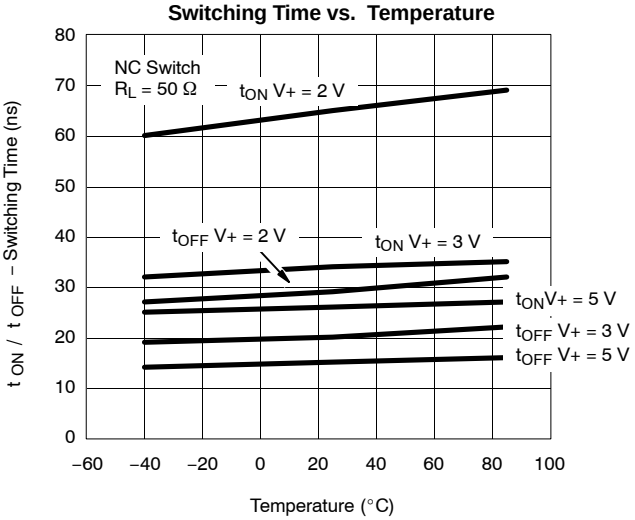


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

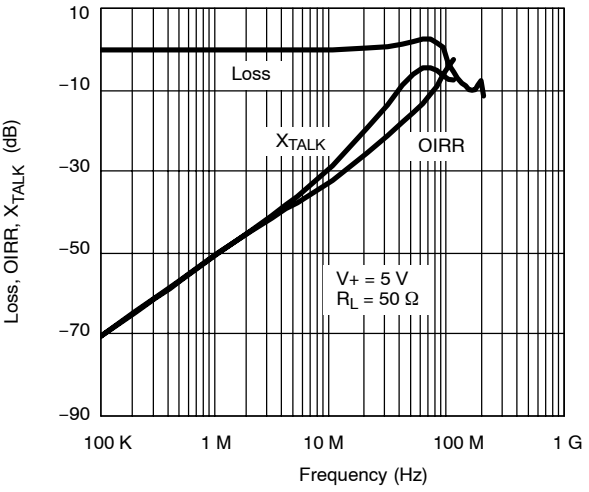
Switching Time vs. Temperature



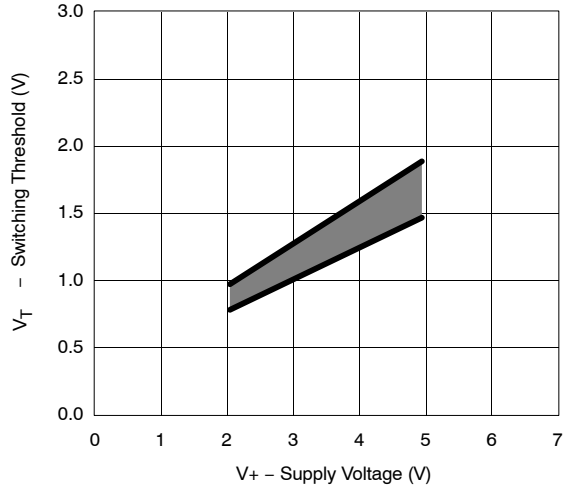
Switching Time vs. Temperature



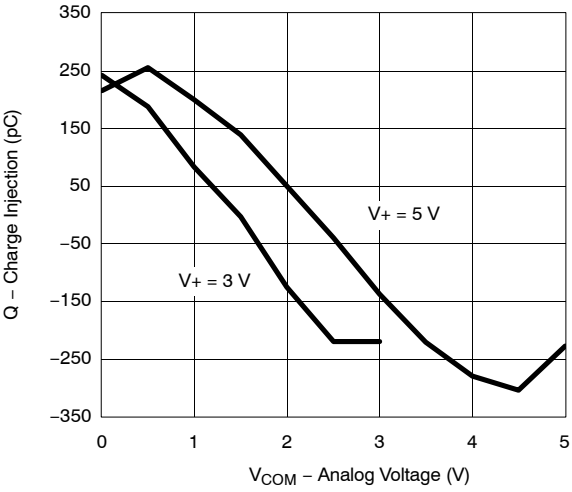
Insertion Loss, Off-Isolation Crosstalk vs. Frequency



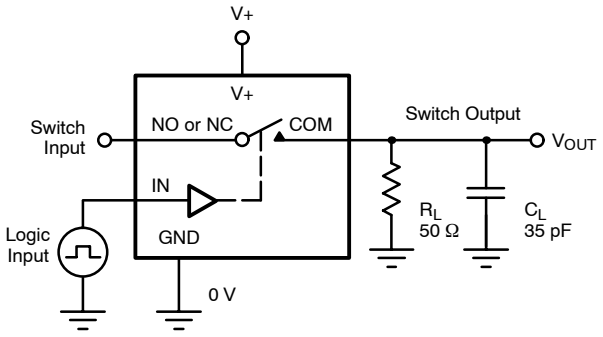
Switching Threshold vs. Supply Voltage



Charge Injection vs. Analog Voltage

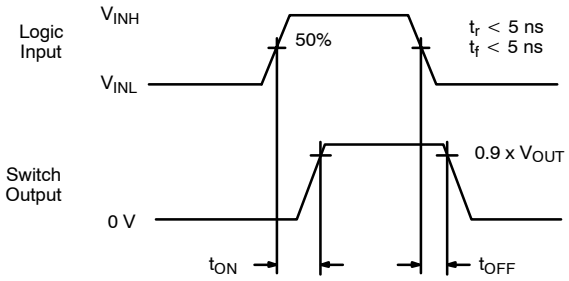


TEST CIRCUITS



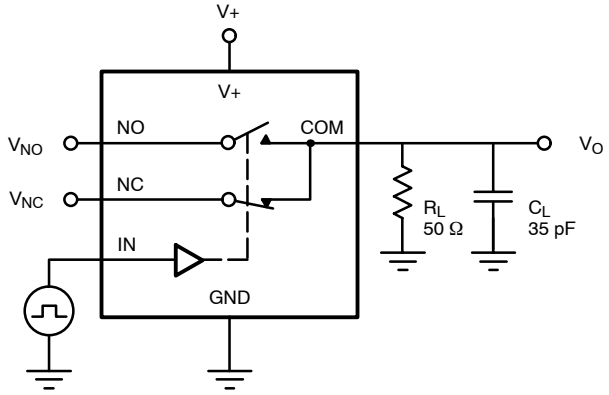
C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM}\left(\frac{R_L}{R_L + R_{ON}}\right)$$



Logic "1" = Switch On
Logic input waveforms inverted for switches that have the opposite logic sense.

FIGURE 1. Switching Time



C_L (includes fixture and stray capacitance)

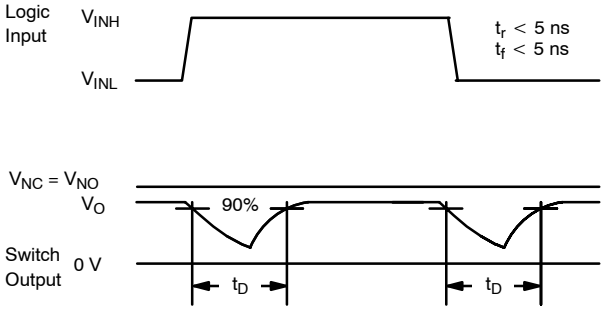
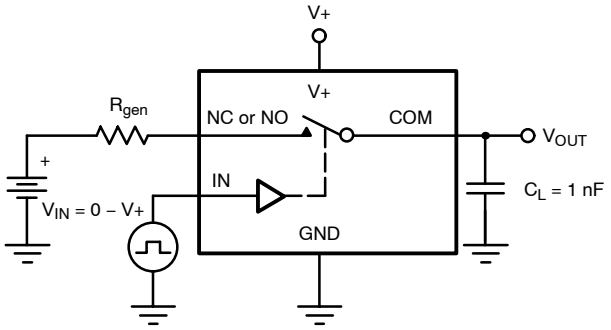
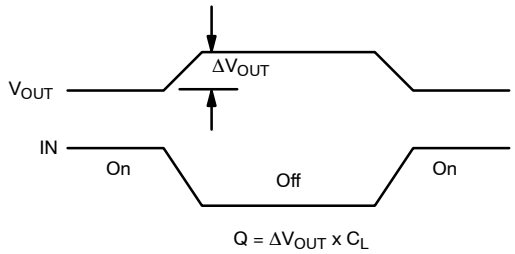


FIGURE 3. Break-Before-Make Interval





$Q = \Delta V_{OUT} \times C_L$

IN depends on switch configuration: input polarity determined by sense of switch.

FIGURE 2. Charge Injection

TEST CIRCUITS

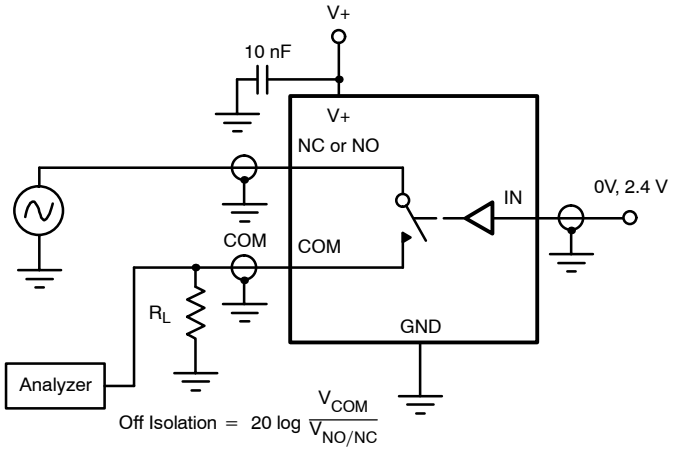


FIGURE 4. Off-Isolation

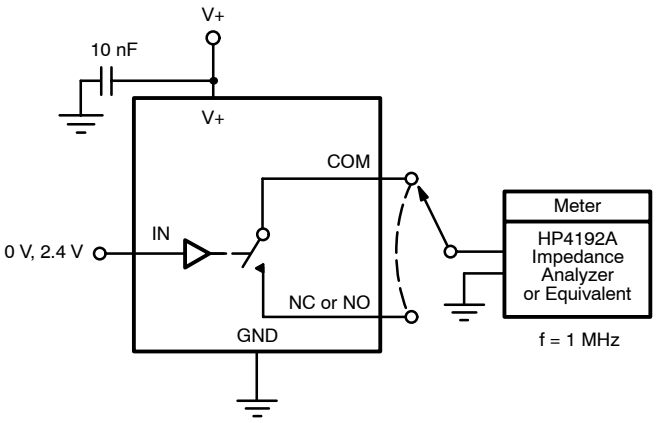


FIGURE 5. Channel Off/On Capacitance

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